

fig. 1

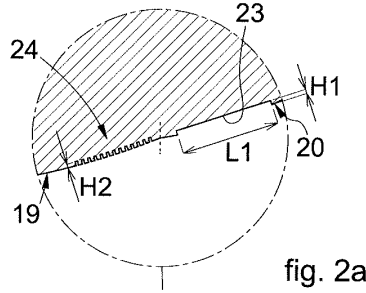


fig. 2a

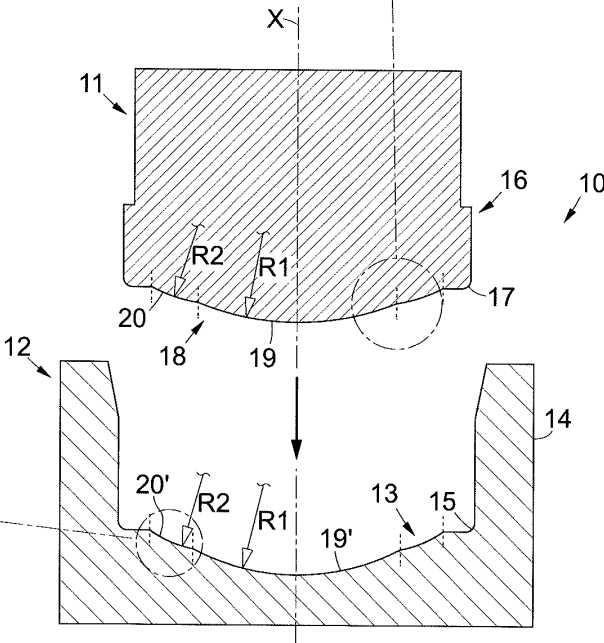


fig. 2

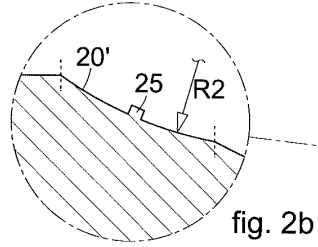


fig. 2b

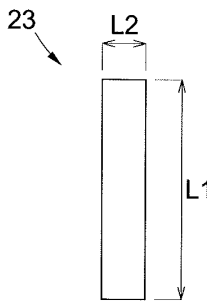


fig. 3a

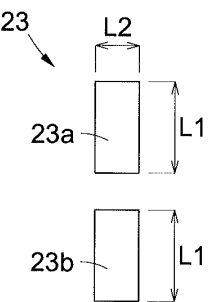


fig. 3b

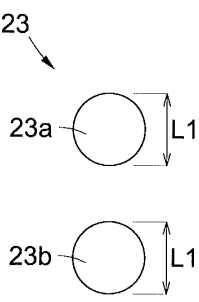


fig. 3c

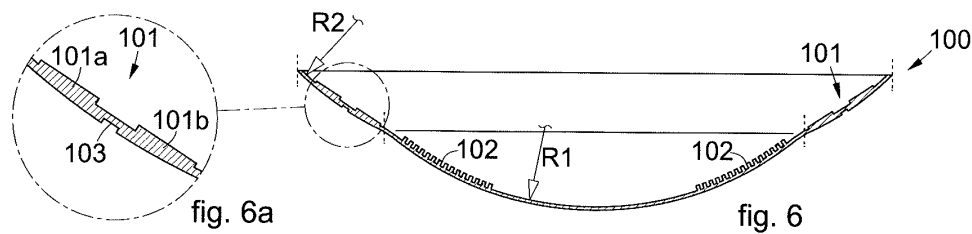
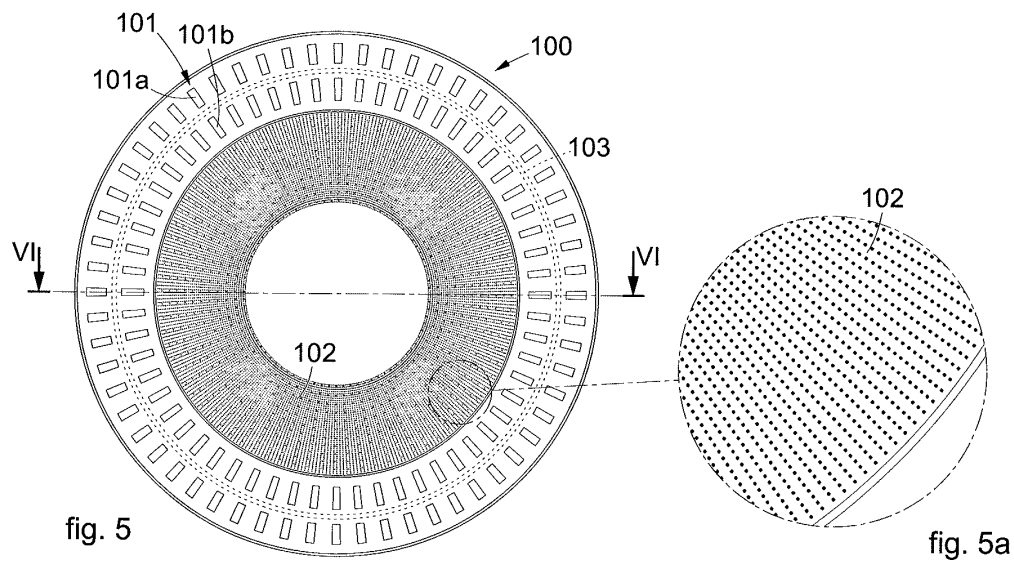
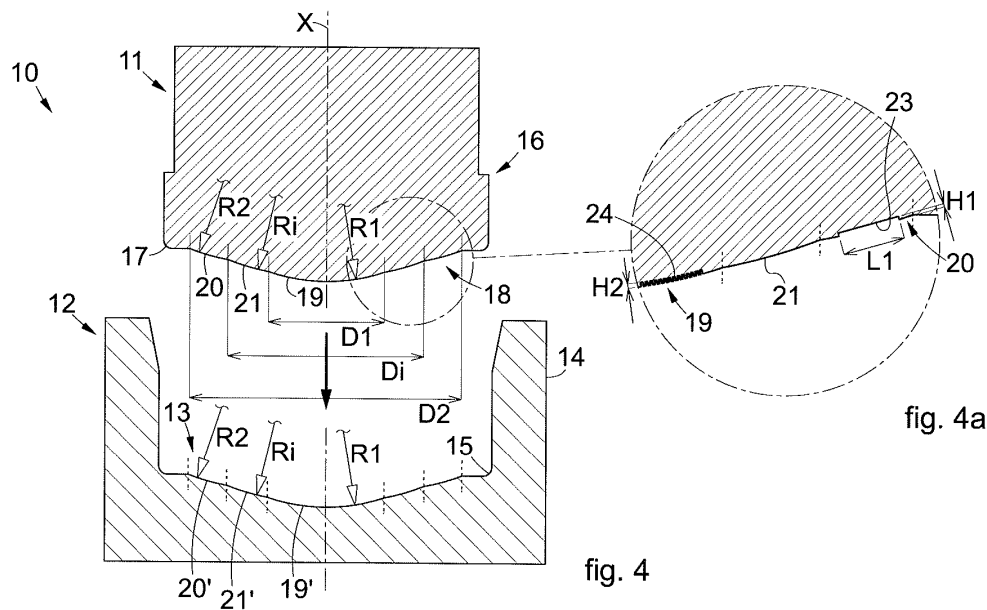


fig. 7b

Figure 1 shows a cross-sectional view of a semiconductor device. The device includes a substrate 11, a gate 12, and a contact 110. A central well 13 is formed in the substrate. The gate 12 is positioned over the well 13. The contact 110 is located on the side of the device. Dimensions D1, D2, D3, D4, and D5 are indicated, representing various lengths and widths of the device components.

fig. 8b